Anti-Resonance and the \0.7 A nom aly" in C onductance through a Quantum Point C ontact

Ye X iong,¹ X.C.X ie,^{1,2} and Shi-Jie X iong³

¹Department of Physics, Oklahom a State University, Stillwater, Oklahom a 74078

²International Center for Quantum Structures and Institute of Physics,

The Chinese Academy of Sciences, Beijing 100080, P.R. China

³Department of Physics, Nanjing University, Nanjing 210093, China

(Dated: April 14, 2024)

We investigate the transm ission of electrons through a quantum point contact by using a quasione-dimensional model with a local bound state below the band bottom. While the complete transm ission in lower channels gives rise to plateaus of conductance at multiples of $2e^2=h$, the electrons in the lowest channel are scattered by the local bound state when it is singly occupied. This scattering produces a wide zero-transm ittance (anti-resonance) for a singlet form ed by tunneling and local electrons, and has no e ect on triplets, leading to an exact 0:75 ($2e^2=h$) shoulder prior to the rst $2e^2=h$ plateau. Form ation of a K ondo singlet from electrons in the Ferm i sea screens the localm om ent and reduces the e ects of anti-resonance, com plem enting the shoulder from 0.75 to 1 at low tem peratures.

PACS num bers: 73,23 Ad, 72.10 Fk, 72.15 Gd

The quantization of conductance in mesoscopic systems has been observed in quantum point contacts (QPC) where a series of plateaus at multiples of 2e²=h appears in curves of conductance G versus gate voltage V_{α} [1, 2]. Prior to the rst integer plateau, a should er of 0.7 ($2e^2=h$) has often been observed and is called the $\setminus 0.7$ anom aly" [3, 4, 5, 6]. Considerable experimental and theoretical e orts have been devoted to understanding this anom aly [7, 8, 9, 10, 11]. In Ref. 10 it is suggested that the anomaly originates from the 3:1 triplet-singlet statistical weight ratio if two electrons form bound states by som e attractive interaction and the triplet has a lower energy. From calculations for two electrons in the Hubbard model or the Anderson Hamiltonian, two resonance peaks in transm ission spectrum are shown, corresponding to singlet and triplet states with weights 0.25 and 0.75 [11]. Som e attention has been focused on the K ondo effect in such system s [12, 13]. In a recent experiment the tem perature and magnetic-eld dependence of the differential conductance was investigated in detail to highlight the connection to the K ondo problem [14], and subsequently a theoretical study was carried out in further support of K ondo physics in QPC [15].

Since relevant states undergo empty, single and double occupations even within the width of one plateau or shoulder, including global charge variations and uctuations in calculations is important. The "0.7 anom aly" appears only prior to the rst integer plateau, and only at relatively higher temperatures, for which the intensity of the K ondo e ect is negligible. The shape of the shoulder ism uch di erent from the two resonance peaks of the singlet and triplet states [11], and there is no evidence of the attractive interaction from which two-electron bound states can be form ed [10]. To address the above m entioned questions, in this Letter we theoretically study the

transport through a quantum point contact (QPC) by using a model which includes the Coulom b interaction, the charge uctuations, and the multi-channel structure on an equal footing. By using the singlet-triplet representation to label spin states of the tunneling electron and the local electron, we show a wide anti-resonance for the singlet channel near the band bottom, giving rise to the 0.75 shoulder. The shoulder is complemented to 1 by the form ation of a K ondo singlet at low tem peratures, and m an ifests itself at higher tem peratures when the K ondo singlet collapses. Thus, the role of the K ondo singlet is to suppress the anti-resonance, quite di erent from the Kondo physics discussed in Ref. [15]. A simple scaling curve for conductance is obtained and is found to com pare wellw ith the experim entalone. The results provide consistent explanations for a wide range of characteristics observed in experiments.

A QPC can be described with a narrow and short bar connected to the left and right leads which serve as reservoirs. Thus, one obtains several continuous 1D subbands. Som e local levels, m ay be virtual bound states [15], can be created by the specic QPC geometry. These states are isolated from the leads and should not be included in the band continuum. The potential of the bar area, including both the band continuum and the local levels, is tuned by the gate voltage. The single-electron energies of subbands and levels are shown in Fig. 1(a). We include on-levelCoulom b repulsion U of electrons con ned in one local state. In equilibrium the Fermi energy of reservoirs is xed and we set it as the energy zero. The occupations of levels is controlled by tuning the gate voltage. In Figs. 1(b), 1(c) and 1(d) we show the empty, single and double occupations of the level nearest the band bottom . W hen the Ferm i level crosses the band bottom , the rst subband contributes to the conductance and the rst

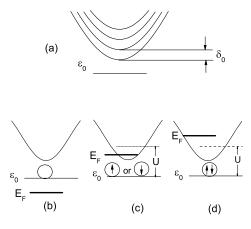


FIG.1: (a) Sketchy illustration of dispersion relation of 1D subbands and local levels. $_0$ is energy spacing between subbands, and $_0$ is the position of the local level. (b) Empty level. E_F denotes the Fermi level. (c) Singly occupied level. (d) D oubly occupied level.

plateau appears. At this moment most of the local levels are fully occupied and have no e ect on the transport, except the one closest to the band bottom which may be singly occupied due to the on-level interaction. It is sufcient to include this level in our model. By tuning V_g further this level is also fully occupied and the plateau structure is determined only by the subbands.

The Hamiltonian of the system can be written as

$$H = \frac{X}{m ; i;} t_0 (a_m^Y ; i, a_m ; i+1; + H c.)$$

$$+ \frac{X}{m ; i;} [(m \quad 1)_0 \quad eV_g] a_m^Y ; i, a_m ; i;$$

$$+ \frac{X}{t^0} (a_{1;0}^Y ; d + H c.) + \frac{X}{(0 \quad eV_g)} d^Y d$$

+
$$U d_{\#}^{Y} d_{\#} d_{\#}^{Y} d_{\#};$$
 (1)

where $a_{m,i}$; and d are the annihilation operators of electrons on the ith site of the m th continuum channel and at the local state, respectively, with being the spin index. $_0$ is the energy spacing between subband bottoms. $_0$ stands for the position of the local level. t_0 is the hopping integral of the channels, and t^0 is the coupling of the local level to the low est channel and the bound state at a site (i = 0). Only the coupling of the local level to the low est channel (m = 1) is considered, because local level coupling has no e ect on the transm ission in higher channels due to the double occupation.

For $V_g = 0$ and at the zero tem perature, the potential is too high and the states in the bar, including the local

state and the continuum chains, are empty. W ith increasing V_g , the local state becomes singly occupied in the range of $_0 < eV_g < _0 + U$. For $eV_g > _0 + U$, it is doubly occupied and has no e ect on the conductance. On the other hand, the m th continuum channel gives $2e^2 = h$ contribution to the conductance if $eV_g > (m - 1)_0 - 2b_0$, because in this case the Ferm i level is higher than the bottom of this subband. This provides the integer plateaus in the G- V_g curves with plateau width $_0 = e$.

Since the local level is below the bottom of the whole band continuum, the tunneling in the rst channel is affected by its charge and spin states. There are 4 states of the local level: the empty, $j_1i = j$, the spin up and down single occupation, $j_2i = j$ "i and $j_3i = j$ #i, and the double occupation, $j_4i = j$ "#i. If an electron is injected into the channel, it will be scattered by the state on the local level. At rst we consider only the tunneling and local electrons and ignore the other electrons in the Ferm isea. These considered electrons form a many-body state

$$j i = \begin{array}{ccc} X^{4} X & O \\ j i = \begin{array}{c} p_{n;1;i;} j_{n} i & jl;i; i; \\ n = 1 & i; \end{array}$$
(2)

where 1; i; i is the orbital at site i with spin in the rst channel, and $p_{n;1;i}$; is the corresponding coe cient. By applying the Hamiltonian on j i one obtains the Schrodinger equations for the coe cients. These equations can be expressed with an equivalent single-particle network in which every site represents a combination of indices (n;1;i;) of the coe cients [16]. In the present case the network is an 8-channel one where every channel stands for a combination of n and , and a site in a channel corresponds to a coordinate i in the chain. In the network the channels with (n = 2; = ") and (n = 3; = #), and the channels with n = 1;4, corresponding to the empty and doubly occupied local states, are independent. The other 2 channels are connected at site i = 0 but can be easily decoupled with the transformation $\mathfrak{F}; \mathfrak{i} \mathfrak{i} = \mathfrak{p}_{\underline{1}}^{1}$ $(\mathfrak{j}_{2}\mathfrak{i}^{\mathsf{N}} \mathfrak{j}; \mathfrak{i}; \sharp \mathfrak{i} \mathfrak{j}_{3}\mathfrak{i}^{\mathsf{N}} \mathfrak{j}; \mathfrak{i}; \mathfrak{i}; \mathfrak{i})$ and $\mathfrak{f}; \mathfrak{i} \mathfrak{i} = \mathfrak{p}_{\underline{2}}^{1}$ $(\mathfrak{j}_{2}\mathfrak{i} \mathfrak{j}; \mathfrak{i}; \sharp \mathfrak{i}; \mathfrak{i}; \mathfrak{i})$. The nal network with 8 independent channels is shown in Fig. 2. For single occupation there is one singlet channel with one scatterer (6) and three pure triplet channels (3, 4, and 5) without scattering by the local level. Dierent from Ref. [10], the singlet-triplet notation used here is m erely to label spin states of the tunneling and local electrons that are not bound together. For > 1 and for the non-scattering pure channels of m = 1, the transm ission coe cient is

$$m() = \begin{array}{ccc} 1; \ \text{for } j & (m & 1)_0 + eV_g j < 2t_0; \\ 0 \ \text{otherw ise.} \end{array} ; \quad (3)$$

where is energy of the injected electron. For the singlet

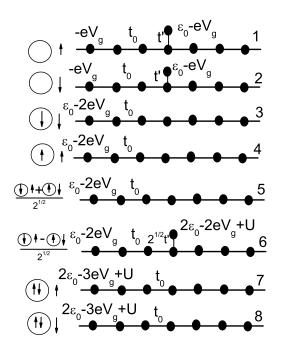


FIG.2: Eight independent channels for a tunneling electron. The state of the local level is illustrated by circles, and the spin of the tunneling electron is represented by an arrow outside the circle.

(em pty) channelofm = 1,

$${}_{s(e)} = \frac{4 \left[u_{s(e)} - 2 \cos(k) \right]^2 \sin^2(k)}{v_{s(e)}^4 + 4 \left[u_{s(e)} - 2 \cos(k) \right]^2 \sin^2(k)}$$
(4)

for $j + eV_g j < 2t_0$ and $_{s(e)} = 0$ otherwise, where k is the momentum of the tunneling electron determined by = $2t_0 \cos(k)$ eV_g , and $u_s = (_0 + U)=t_0$, $u_e = _0=t_0$, $v_s = 2t_0 - t_0$, $v_e = t_0 - t_0$.

For the singlet channel the scatterer produces an antiresonance at = $_0$ eV_a + U with a zero transm ission coe cient at the minimum and with semi-width $t^{02} = t_0 jsin(k) j$. Near the subband bottom where we fo-0, so the width of the dip is extremely cus, sin(k) large even though t^0 m ay be much smaller than t_0 . As a result, the dip of $_{\rm s}$ develops to a the plateau with nearly zero height. This is di erent from the results of Ref. [11] where the singlet and triplet states give two separate resonance peaks with di erent weights. Without the magnetic eld and ignoring the e ects of other electrons, in the range of single occupation comma the conductance is governed by $e^2=2h$ times the sum of the transm ission coe cients of the singlet and triplet channels which are non-zero only for the tunneling electron with energy higher than the subband bottom . Here the prefactor 1=2 stands for the weight of one spin state of the local electron. As mentioned above, $_0$. 2ta, so

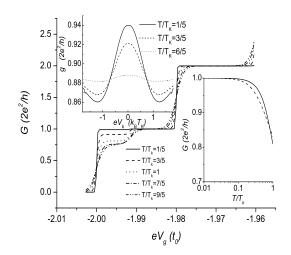


FIG.3: Linear conductance as a function of the gate voltage. The parameters are: $_0 = 0.02t_0$, $U = 0.016t_0$, $_0 = 2.008t_0$, $T_K = 0.0005t_0$ and $t^0 = 0.05t_0$. Upper inset: D i erential conductance as a function of bias voltage for $eV_g = 1.993t_0$. Low er inset: Linear conductance as a function of scaled tem – perature $T = T_K$. Solid line: The calculated conductance.

 $_0$ + U may be above the subband bottom . Thus, in the range of 2t < eV_g < $_0$ + U conductance plateaus at height 0:75(2e²=h). For eV_g > $_0$ + U, the conductance is dom inated by the double-occupation channels (7 and 8 in Fig. 2), leading to a jump from 0.75 to 1 at eV_g = $_0$ + U. This is the origin of the 0.7 anom aly within ourm odel.

Now we consider the electrons in the Ferm i sea. It is known that at low tem peratures the electrons from Ferm isea are coupled with the local electron to form a K ondo singlet. In this case the local state is screened by the Ferm i electrons and is no longer available for the injected electron in the singlet channel, resulting in the disappearance of the side-coupled scatterer for this channel. This removes the anti-resonance and enhances the transmission coe cient from nearly zero to one. If the probability of annihilating the K ondo singlet is p_k , the average transm ission coe cient of the singlet channel is $s = (1 p_k)_1 + p_k s$. We choose $p_k = \tanh(T = T_K)^2$. This simple form rejects the physics that at low temperature the K ondo singlet peak in the spectral density goes T^2 [18]. The form ation of the K ondo singlet has as 1 no e ect for the triplet channels since they are without scattering.

Combining all the contributions, the linear conductance at temperature T can be calculated as

$$G(T) = \frac{2e^2}{h}^Z d \frac{Qf(jT)}{Q} (j; (5))$$

$$() = P_0 (T)_e () + P_2 (T)_1 ()$$

$$+ \frac{P_{1}(T)}{4} [s() + 3_{1}()] + X_{m}();$$

where f(;T) is the Ferm i-D irac distribution, $P_1(T)$ is the therm alprobability of nding the local level occupied by lelectrons,

$$P_{1}(T) = \frac{2}{Z} e^{-\frac{0}{k_{B}T}}; P_{2}(T) = \frac{1}{Z} e^{-\frac{2}{0}\frac{2eV_{g}+U}{k_{B}T}};$$

$$P_{0}(T) = \frac{1}{Z}; Z = 1 + 2e^{-\frac{0}{k_{B}T}} + e^{-\frac{2}{0}\frac{2eV_{g}+U}{k_{B}T}}: (6)$$

In Fig. 3 we plot the conductance as a function of the gate voltage for several values of T. The local level $_0$ is below and close to the band bottom, $_0$ + U is above it, and t^0 $_{0}$, re ecting the localized nature of the level. The value of t_0 = $_0$ corresponds to the num ber of channels. A 0:75 shoulder is clearly seen at high tem peratures T > T_K , m eanwhile it is complemented to 1 at low tem – peratures T < T_K . This accounts for the basic features observed in the recent experiment [14].

At low tem peratures P_1 and f () can be approximated with step functions and for $\ 2t_g < eV_g < \ _0 + U$, Eq. (5) becomes

G (T) =
$$\frac{2e^2}{h}$$
 $\frac{3}{4}$ + $\frac{1}{4}$ F (P) ; (7)

where F (P) is a universal function of rescaled tem perature $\mathbf{\hat{F}} = \mathbf{T} = \mathbf{T}_{K}$, describing the in uence of the K ondo e ect. Here, the range of F is [0;1], the prefactor of F is 1=4 and the constant is 3=4, rejecting the fact that the form ation of the K ondo singlet in uences only the contribution from the singlet channel. In Ref. [14], the same functional form as Eq.(7) is used for G (T), how ever, the corresponding prefactor and constant are both 1=2. But the range in which the measured points can be tted well by a universal function is only from 1=2 to 1, as can be seen from Fig. 2(b) in Ref. [14]. This implies that the experimental data only con m the 1=4 of the conductance that is in uenced by the K ondo e ect. The other 1=4 m ay also vary with tem perature but perhaps due to other physical in uences. In Ref. [17], from the data of quantum dots the prefactor is 1 and the constant is 0, implying the full K ondo e ect for the tunneling. This m ay indicate the consequence of di erent structures between a QPC and a quantum dot: the K ondo im purity is an extra local level in QPC as studied in this work while it may be embedded in the tunneling path in quantum dots. It is known that there is no anti-resonance associated with the latter case [19]. It is easy to see that at low T F (P) 1 p(T) = 1 tanh ($T = T_{K}^{2}$)². In the lower inset of Fig. 3 we show (solid line) the scaling conductance of Eq.(7). For a com parison, the experim entally obtained scaling conductance (dashed line) is also shown. The experim ental conductance is obtained from

Eq.(1) and Eq.(2) of Ref. [14]. The experimental T_K is twice the value of the theoretical one.

By applying a bias voltage V_b between two leads the current is $I = \frac{2e}{h}K$ d [f ($eV_{E}=2$) f ($+eV_{E}=2$)] (), function F (F) in Eq.(7) becomes F (F) exp[$(eV_b=w)^2$], re ecting the width w ($k_B T_K$) of the K ondo peak in the spectral density [20]. We calculate the di erential conductance $g = \frac{dI}{dV_b}$, shown in the upper inset of F ig. 3. The zero-bias peak, originated from the Ferm i-level dependence of the K ondo e ect, exists only at low tem – peratures for which the 0.7 shoulder is com plem ented to 1. By applying a magnetic eld, the degeneracy of spins is lifted, and the spin of the local level is along the eld direction. As a result, the singlet-triplet representation is no longer suitable and all the plateaus becom e multiples of 0.5 ($2e^2=h$) due to the splitting of spin subbands.

In sum m ary, we demonstrate that a combination of anti-resonance of the singlet channel and K ondo physics provides a satisfying account of basic features associated with the "0.7 anom aly" in quantum point contacts.

We thank Junren Shi for helpful conversations. This work is supported by DOE Grant No. DE/FG02-04ER46124, NSF-EPSCoR, and NSF-China.

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